

08/064,212, filed May 12, 1993, now abandoned, which is itself a divisional of 07/842,758, filed February 28, 1992, now abandoned, which is itself a continuation of 07/595,762, filed October 3, 1990, now abandoned, which is itself a continuation of 07/312,420, filed February 21, 1989, now abandoned, which is itself a continuation of 07/092,130, filed September 2, 1987, now abandoned, which is itself a divisional of 06/801,768, filed November 26, 1985, now abandoned.--

IN THE CLAIMS:

Please amend claims 13, 16, 17, and 20 as follows:

13. (Amended) A vapor reaction method comprising the steps of:
- preparing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged substantially in parallel with each other;
 - placing a substrate in a reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;
 - introducing a first film forming gas into said reaction chamber through said second electrode;
 - exciting said first film forming gas in order to form a first insulating film by vapor deposition on said substrate placed in said reaction chamber;
 - introducing a second film forming gas into said reaction chamber through said first electrode;

exciting said second film forming gas in order to form a second insulating film by vapor deposition on said first insulating film in said reaction chamber;

removing said substrate from said reaction chamber after said vapor deposition;

introducing a cleaning gas into said reaction chamber through said second electrode;

exciting said cleaning gas in order to perform a [plasma] cleaning on at least a portion of said pair of electrodes.

16. (Amended) A vapor reaction method comprising the steps of:

preparing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged, substantially in parallel with each other;

placing a substrate in a reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through said second electrode;

exciting said first film forming gas in order to form a [SiO₂] first film comprising SiO₂ by vapor deposition on said substrate placed in said reaction chamber;

introducing a second film forming gas into said reaction chamber through said second electrode;

exciting said second film forming gas in order to form a second film in said reaction chamber;

removing said substrate from said reaction chamber after said vapor deposition;

introducing a cleaning gas into said reaction chamber through said second electrode;

exciting said cleaning gas in order to perform a [plasma] cleaning on at least a portion of said pair of electrodes.

17. (Amended) A vapor reaction method comprising the steps of:

preparing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged substantially in parallel with each other;

placing a substrate in a reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through said second electrode;

exciting said first film forming gas in order to form a [SiO₂] first film comprising SiO₂ by vapor deposition on said substrate placed in said reaction chamber;

introducing a second film forming gas into said reaction chamber through said second electrode;

exciting said second film forming gas in order to form a [boronsilicate glass] second film by vapor deposition on said [SiO₂] first film in said reaction chamber;

introducing a cleaning gas into said reaction chamber through said second electrode;

exciting said cleaning gas in order to perform a [plasma] cleaning on at least a portion of said pair of electrodes.

20. (Amended) The method of claims 3, 6, 9, 11, 13, 16, 17 or 18 wherein said [fluoride is] cleaning gas comprises nitrogen fluoride.

Please add new claims 21-30 as follows:

--21. A method of fabricating electronic devices comprising the steps of:
preparing a pair of electrodes within a reaction chamber wherein said pair of electrodes are opposed in parallel with each other;
placing a substrate in a reaction chamber wherein said substrate is held by one of said electrodes;
introducing a first film forming gas into said reaction chamber through the other one of said electrodes;
exciting said first film forming gas to form a first film by first chemical vapor deposition on said substrate;
introducing a second film forming gas into said reaction chamber through the other one of said electrodes;
exciting said second film forming gas to form a second film by second chemical vapor deposition on said first film;

introducing a cleaning gas into said reaction chamber through said other one of the electrodes; and

conducting a cleaning of an inside of said reaction chamber by using said cleaning gas to remove layers caused by at least said first and second vapor phase deposition.

22. A method according to claim 21 wherein said first chemical vapor deposition is a photo CVD.

23. A method according to claim 21 wherein said second chemical vapor deposition is a plasma CVD.

24. A method according to claim 21 wherein said cleaning gas is excited by said pair of electrodes.

25. A method according to claim 21 wherein said other one of the electrodes is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.

26. A method of fabricating electronic devices comprising the steps of:
preparing a pair of electrodes within a reaction chamber wherein said pair of electrodes are opposed in parallel with each other;

placing a substrate in a reaction chamber wherein said substrate is held

the other one of said electrodes;

exciting said first film forming gas to form a first film by first chemical vapor deposition on said substrate;

introducing a second film forming gas into said reaction chamber through the other one of said electrodes;

exciting said second film forming gas to form a second film by second chemical vapor deposition on said first film wherein said second film comprises a different material from said first film;

removing said substrate from said reaction chamber after the formation of said first and second films;

introducing a cleaning gas into said reaction chamber through said other one of the electrodes; and

conducting a cleaning of an inside of said reaction chamber by using said cleaning gas to remove layers caused by at least said first and second vapor phase deposition.

27. A method according to claim 26 wherein said first chemical vapor deposition is a photo CVD.

28. A method according to claim 26 wherein said second chemical vapor deposition is a plasma CVD.

29. A method according to claim 26 wherein said cleaning gas is excited by said pair of electrodes.